



Description

The HXY4866DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 40V$ $I_D = 33A$

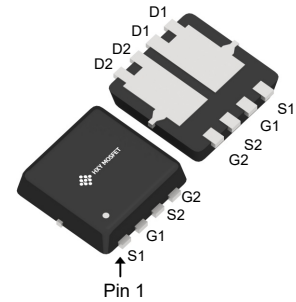
$R_{DS(ON)} < 15m\Omega$ @ $V_{GS}=10V$

Application

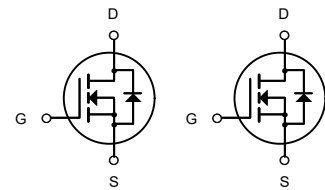
Battery protection

Load switch

Uninterruptible power supply



DFN3X3B-8L



Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY4866DF	DFN3X3B-8L	4866 XXX YYYY	5000

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	33	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	21	A
I_{DM}	Pulsed Drain Current	55	A
EAS	Single Pulse Avalanche Energy	22.1	mJ
IAS	Avalanche Current	10	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation	2	W
TSTG	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	60	$^{\circ}C/W$



Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=6A$	---	13	15	$m\Omega$
		$V_{GS}=4.5V$, $I_D=5A$	---	19	23	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	1.7	2.4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=32V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=12A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.1	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=32V$, $V_{GS}=4.5V$, $I_D=6A$	---	3.8	---	nC
Q_{gs}	Gate-Source Charge		---	2.8	---	
Q_{gd}	Gate-Drain Charge		---	1.1	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=1A$	---	12.2	---	ns
T_r	Rise Time		---	5.3	---	
$T_{d(off)}$	Turn-Off Delay Time		---	18	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	376	---	pF
C_{oss}	Output Capacitance		---	240	---	
C_{rss}	Reverse Transfer Capacitance		---	19	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	33	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=6A$, $dI/dt=100A/\mu s$, $T_J=25^{\circ}\text{C}$	---	20	---	nS
Q_{rr}	Reverse Recovery Charge		---	35	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=10A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

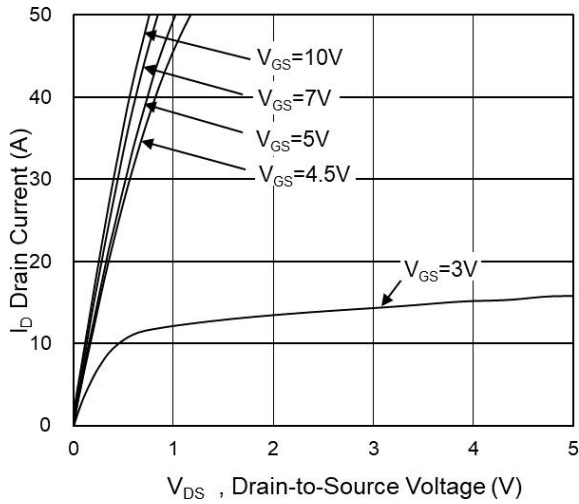


Fig.1 Typical Output Characteristics

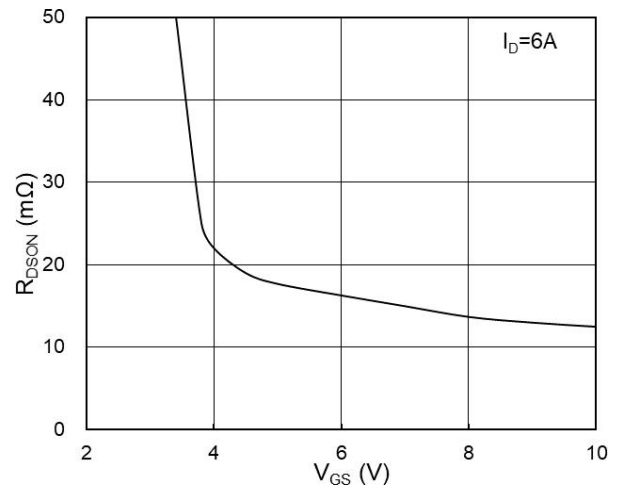


Fig.2 On-Resistance vs G-S Voltage

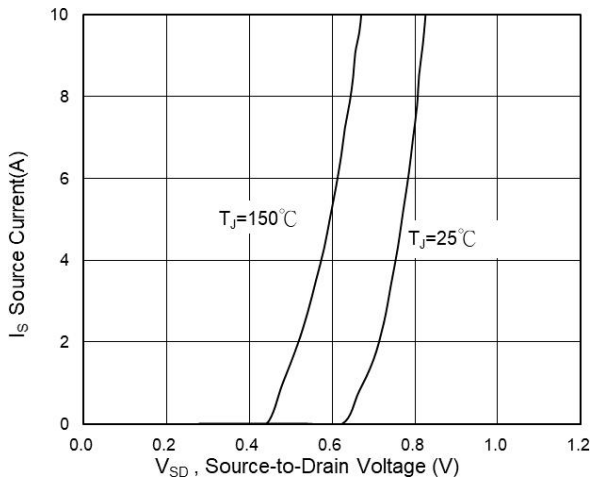


Fig.3 Source Drain Forward Characteristics

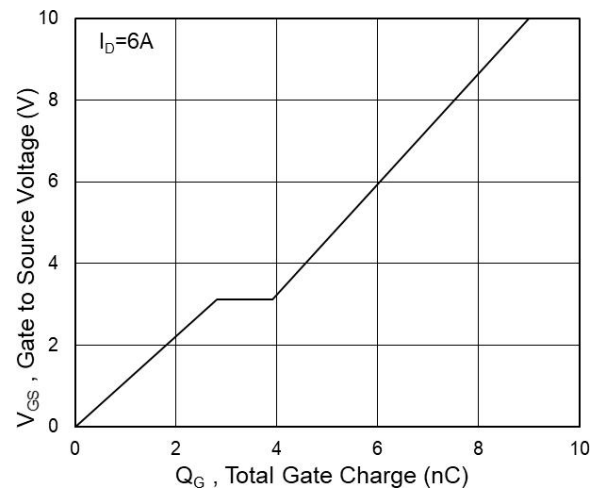


Fig.4 Gate-Charge Characteristics

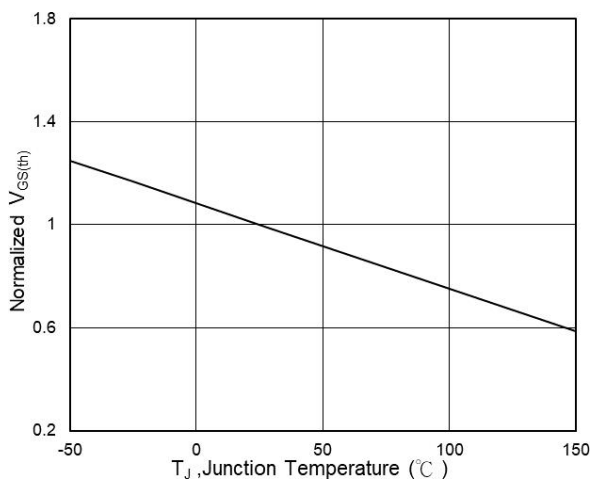


Fig.5 Normalized $V_{GS(th)}$ vs T_J

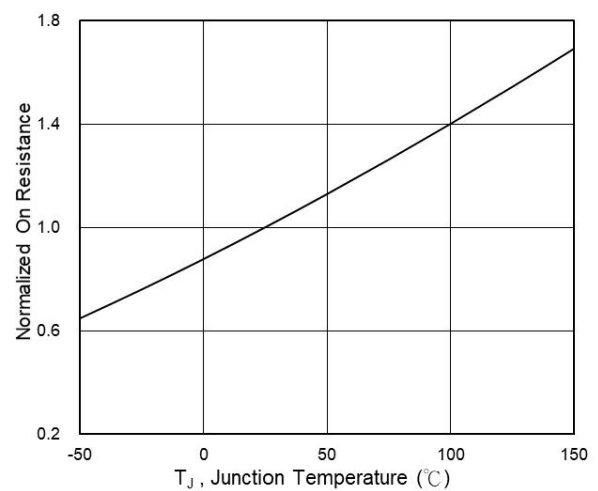


Fig.6 Normalized $R_{DS(on)}$ vs T_J

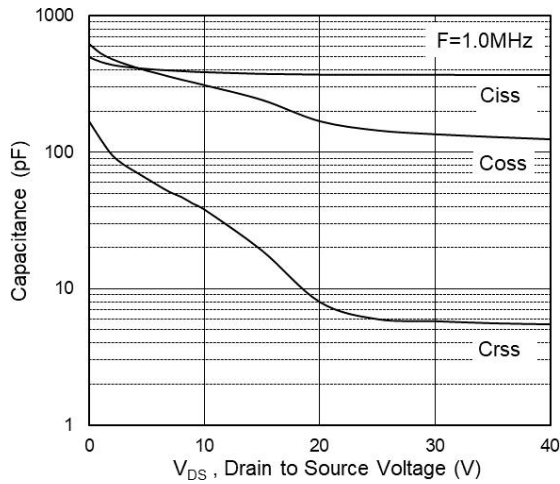


Fig.7 Capacitance

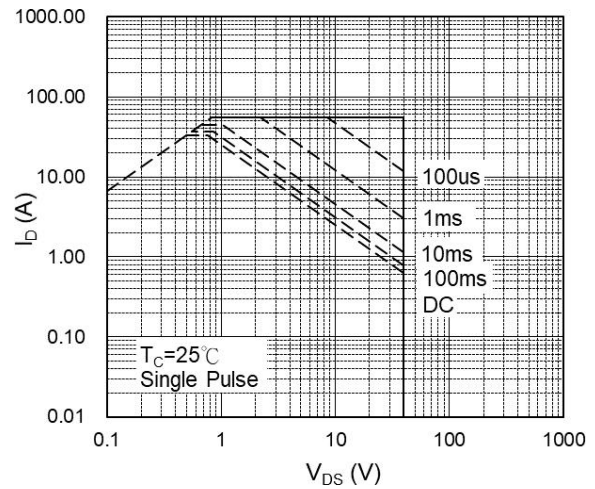


Fig.8 Safe Operating Area

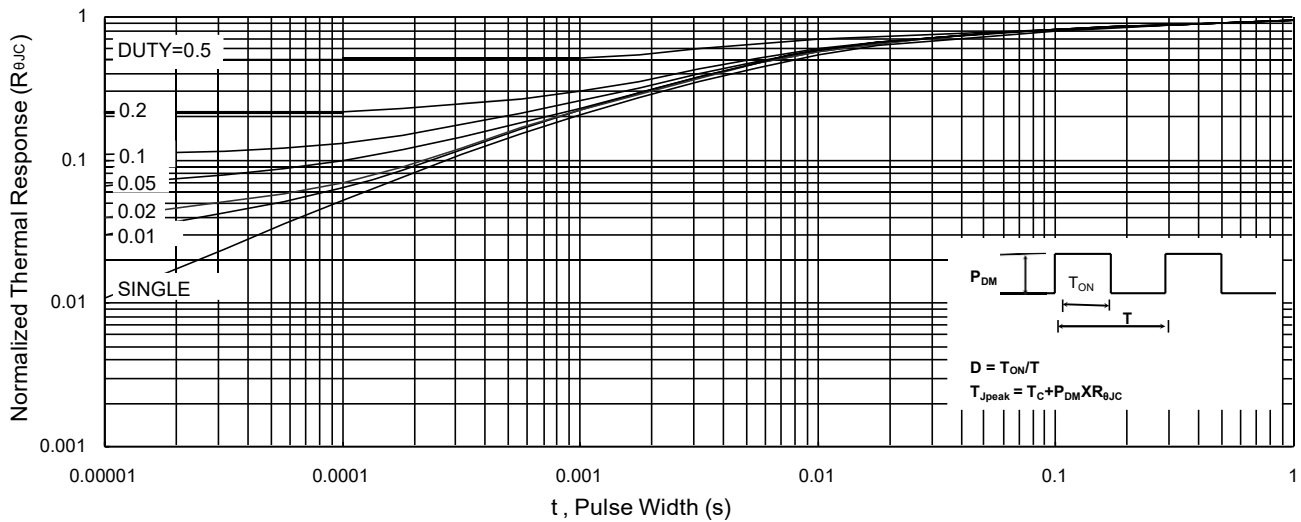


Fig.9 Normalized Maximum Transient Thermal Impedance

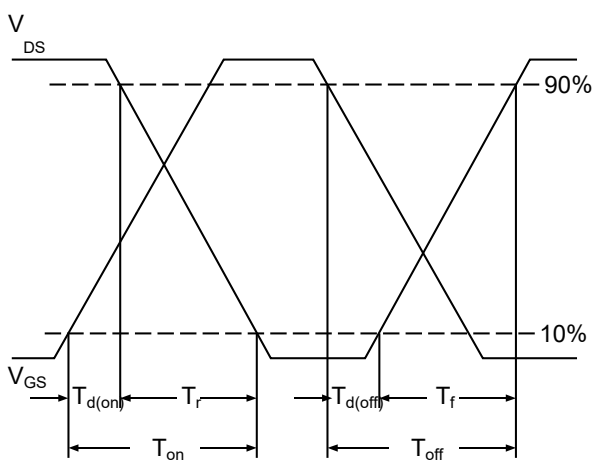


Fig.10 Switching Time Waveform

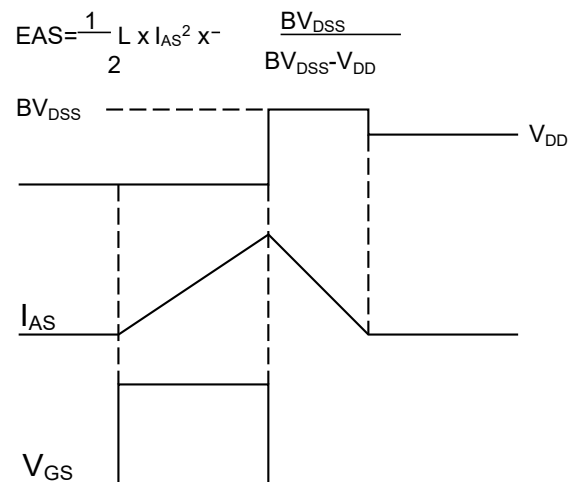
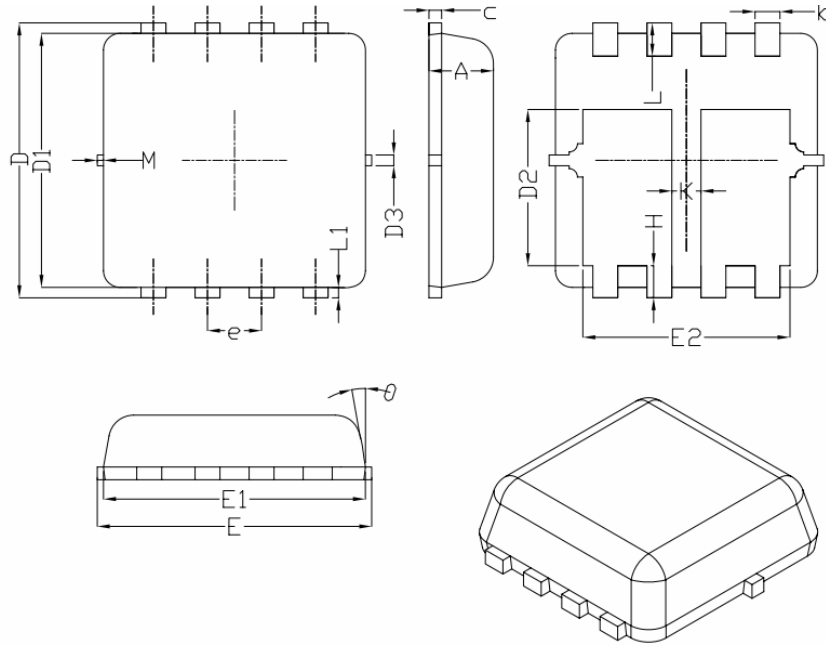


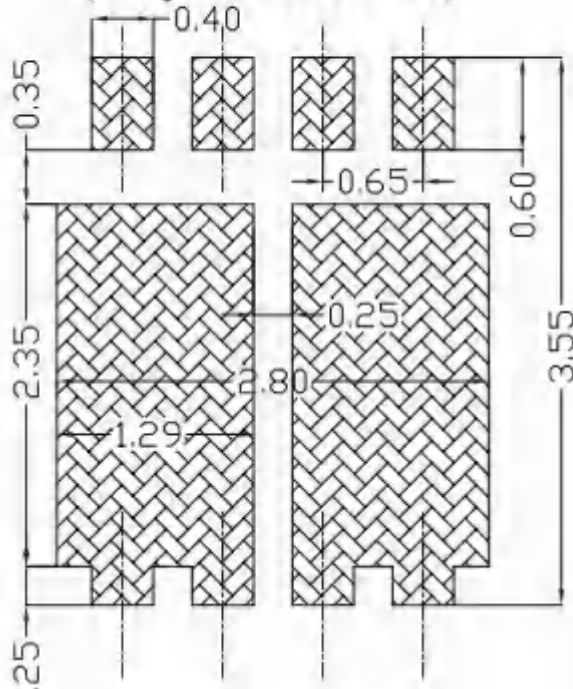
Fig.11 Unclamped Inductive Switching Waveform



DFN3X3B-8L Package Information



Land Pattern
(Only for Reference)



SYMBOL	DIMENSIONAL REOMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
K	0.30	---	---
θ	---	10°	12°
M	*	*	0.15
* Not specified			



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